

Table of Contents

Preface, Committee and Acknowledgement

Chapter 1: Cleaning for FEOL Applications

Necessity of Cleaning and its Application in Future Memory Devices G.M. Choi	3
Removal of Interfacial Layer in HfO₂ Gate Stack by Post-Gate Cleaning Using NF₃/NH₃ Dry Cleaning Technique M.S. Lee, H.J. Oh, J.H. Lee, I.G. Lee, W.G. Shin, S.Y. Kang and D.H. Ko	11
Catalyst Assisted Low Temperature Pre Epitaxial Cleaning for Si and SiGe Surfaces S.K. Dhayalan, A. Hikavy, R. Loo, K. Wostyn, K. Kenis, Y. Shimura, E. Rosseel, H.B. Profijt, J.W. Maes, B. Douhard and W. Vandervorst	16
HF-Last Wet Clean in Combination with a Low Temperature GeH₄-Assisted HCl <i>In Situ</i> Clean Prior to Si_{0.8}Ge_{0.2}-on-Si Epitaxial Growth K. Wostyn, S.K. Dhayalan, A. Hikavy, R. Loo, B. Douhard, A. Moussa, D. Rondas, K. Kenis, P.W. Mertens, F. Holsteyns, S. De Gendt and H.B. Profijt	20
Retardation Phenomenon of Oxide Removal during the Formation of Dual Gate Oxide via PR-Mask Wet Etching K.H. Ko, M.G. Song, B.K. Cho, B.U. Yoon, Y.J. Cho and T. Kim	24
Aluminum Reduction in SC1 S.J. Kweskin and L.W. Shive	28
Metal Removal Efficiency in Deep Submicron Trenches by Wet Chemicals P. Garnier, N. Drogue and R. Duru	32
Impact of Surface Treatment of Si₃N₄ on Subsequent SiO₂ Deposition F. Milanesi, S. Vendrame, E. Ravizza, S. Spadoni, F. Pipia and L. Livellara	36
Operation of a New Electrolyzed Cell Using Boron Doped Diamond Electrodes M. Fryda, T. Mathée, J. Oshinowo, D.H. Baek, H.J. Förster and G. Heinze	40

Chapter 2: Cleaning for FEOL Applications: Beyond-Si Active Area

InGaAs (110) Surface Cleaning Using Atomic Hydrogen T. Kent, M. Edmonds, R. Droopad and A.C. Kummel	47
Surface Chemistry of GaAs(100) and InAs(100) Etching with Tartaric Acid P. Mancheno-Posso and A.J. Muscat	52
Nanoscale Etching and Reoxidation of InAs D.H. van Dorp, S. Arnauts, D. Cuypers, J. Rip, F. Holsteyns and S. De Gendt	56
Passivation of InSb(100) with 1-Eicosanethiol Self-Assembled Monolayers Y. Contreras and A.J. Muscat	59
Cross-Contamination Risk Evaluation during Fabrication of III-V Devices in a Silicon Processing Environment M.C. Roure, S. Vialle, M. Rebaud, H. Fontaine and P. Besson	63
Surface Cleaning of Graphene by CO₂ Cluster H.M. Choi, J.A. Kim, Y.J. Cho, T.Y. Hwang, J.W. Lee and T. Kim	68

Chapter 3: Wet Etching for FEOL Applications

Process Control Challenges of Wet Etching Large MEMS Si Cavities I. Kashkoush, J. Rieker, G. Chen and D. Nemeth	73
Wet Etch Rate Behavior of Poly-Si in TMAH Solution at Various Ambient Gas Conditions E. Lin, T. Guo, C.C. Chien, M.H. Chang, W. Yu, N.H. Yang, J.F. Lin, J.Y. Wu, K.M. Robb, A. Baldaro and A.N. Other	78

Advanced Monitoring of TMAH Solution J.J. Wang, E. Shalyt, C.N. Bai, G. Liang, M. MacEwan and V. Parekh	81
Effect of Dissolved Oxygen for Advanced Wet Processing Y. Yoshida, M. Otsuji, H. Takahashi, J. Snow, F. Sebaai, F. Holsteyns, P.W. Mertens, M. Sato, H. Shirakawa and H. Uchida	85
Watermark Formation on Bare Silicon: Impact of Illumination and Substrate Doping A.H. Tamaddon, H. Philipsen, P.W. Mertens, F. Holsteyns, M. Heyns, S. De Gendt and D.H. van Dorp	89
Selective Nitride Etching with Phosphoric and Sulfuric Acid Mixtures Using a Single-Wafer Wet Processor V. Sih, B. Reimer, A.S. Ratkovich, J.M. Lauerhaas and J.W. Butterbaugh	93
Single Wafer Selective Silicon Nitride Removal with Phosphoric Acid and Steam T. Guo, W. Yu, C.C. Chien, E. Lin, N.H. Yang, J.F. Lin, J.Y. Wu, A. Ratkovich, D. Kahaian, J.W. Butterbaugh and J.M. Lauerhaas	97
Pt Etching Method at Low Temperature Using Electrolyzed Sulfuric Acid Solution Y. Ogawa, M. Uchida, T. Otsu, T. Nagai and H. Morita	101
Nickel Selective Etch for Contacts on Ge Based Devices F. Sebaai, L. Witters, F. Holsteyns, Y. Yukifumi, P.W. Mertens and S. De Gendt	105

Chapter 4: Wet Processing of High Aspect Ratio Structures

Study of Wetting of Nanostructures Using Decoration by Etching G. Vereecke, X.M. Xu, E. Kesters, I. Simms, K. Nafus, L. Haensel, T.G. Kim, M. Lismont, F. Holsteyns and S. De Gendt	111
Impact of Electrostatic Effects on Wet Etching Phenomenon in Nanoscale Region A. Okuyama, S. Saito, Y. Hagimoto, K. Nishi, A. Suzuki, T. Toshima and H. Iwamoto	115
Freeze Drying of High Aspect Ratio Structures M.N. Patel, S. Sirard, R. Limary and D. Hymes	119

Chapter 5: Fluid Dynamics, Cleaning Mechanics

Effect of DI-Water Dilution and Etchant Arm Movement on Spinning Type Wet Etch H.H. Lee, D. Ahn, S.T. Lim and T. Kim	125
Effect of Nozzle Distance and Fluid Flow Rate in Jet Spray Wafer Cleaning Process K.M. Seo, D.H. Kim, Y.J. Cho and T.H. Kim	128
Effects of Chamber Pressure on the Performance of CO₂ Beam Cleaning S.H. Kim, J.H. Lee and H.Y. Kim	131
Physical Chemistry of Water Droplets in Wafer Cleaning with Low Water Use J.C.J. van der Donck, J. Bakker, J.A. Smeltink, R.B.J. Kolderweij, B.C.M.B. van der Zon and M.H. van Kleef	134
Metal Etch in Advanced Immersion Tank with Precision Uniformity Using Agitation and Wafer Rotation S. Tice and C.G. Park	138
Novel Slurry Injection System for Improved Slurry Flow and Reduced Defects in CMP A. Philipossian, L. Borucki, Y. Sampurno and Y. Zhuang	143
Effect of Viscoelasticity of PVA Brush on Friction during Post-CMP Cleaning: A Guideline for Nodule Configuration Y. Hara, T. Sanada, A. Fukunaga and H. Hiyama	148
Understanding the Formation of Circular Ring Defects in Post-CMP Cleaning P. Hsu, R. Luo and P. Berar	153
Particle Measurement with a Liquid-Borne Particle Counter: Analytical Figures of Merit S. Liu and B. Liu	157
Fluid Flow and Defect Density Considerations when Drying Bumped Wafers Using Spin and Surface Tension Gradient Methods D.L. Goodman, D. Rabideau and M. Sobhian	161

Characterization of Cavitation in Ultrasonic or Megasonic Irradiated Gas Saturated Solutions Using a Hydrophone	
M. Zhao, R. Balachandran, P.R. Madigappu, P. Yam, C. Zanelli, R. Sierra and M. Keswani	165
Detection of HO₂•/O₂• Radicals Formed in Aqueous Solutions Irradiated with Megasonic Waves Using a Cavitation Threshold (CT) Cell Set-Up	
Z.X. Han, B. Wu, I. Brown, M. Beck and S. Raghavan	170

Chapter 6: Photo Resist Performance and Rework

Photo Lithography - Surface Preparation Interactions	
P. Garnier	177
Study of Etchants' Diffusion into a 248 nm Deep UV Photoresist during a Wet Etch	
M. Foucaud, N. Rochat, P. Garnier, E. Pargon and R. Tiron	183
Megasonic Enhanced Photoresist Strip with DiO₃	
D. Dussault, J. Fittkau and C. Gottschalk	187

Chapter 7: Cleaning for BEOL Interconnect Applications

Wetting Behavior of Plasma Etch Residue Removal Solutions on Plasma Damaged and Repaired Porous ULK Dielectrics	
N. Ahner, S. Zimmermann, N. Köhler, S. Krüger and S.E. Schulz	193
Effect of Downstream Plasma Treatment on Dissolution of Fluorocarbon Polymer in Organic Solvents	
Q.T. Le, E. Kesters, J. Devonport, F. Holsteys and S. De Gendt	197
Post Etch Residue Removal and Material Compatibility in BEOL Using Formulated Chemistries	
E. Kesters, Q.T. Le, D. Yu, M. Shen, S. Braun, A. Klipp and F. Holsteys	201
Characterization of Cu-BTA Organic Complexes on Cu during Cu CMP and Post Cu Cleaning	
B.J. Cho, J.G. Park, S. Shima and S. Hamada	205
TiN Hard Mask Cleans with SC1 Solutions, for 64nm Pitch BEOL Patterning	
L. Broussous, D. Krejcirova, K. Courouble, S. Zoll, A. Iwasaki, H. Ishikawa, F. Buisine, A. Lamaury and D. Fuard	209
Industrial Challenges of TiN Hard Mask Wet Removal Process for 14nm Technology Node	
A. Iwasaki, K. Courouble, S. Lippy, F. Buisine, H. Ishikawa, E. Cooper, E. Kennedy, S. Zoll and L. Broussous	213
TiN Metal Hardmask Residue Removal Formulation Development for Advanced Porous Low-K and Cu Interconnect Application	
H. Cui	217
Prevention of Unexpected Oxidation of Metal Layer by Removing Hydrogen Peroxide from Ultrapure Water and Diluted Hydrofluoric Acid	
D. Yaon, M. Murayama, H. Kobayashi and K. Yamanaka	221
Cost-of-Ownership Comparison of Single-Wafer Processes for Stripping Copper Pillar Bump Photomasks	
H.S. Sohn, T.K. Hua, D. Liang, S.L.H. Jang, L.W. Leng, H.M. Lin and J. Tracy	225

Chapter 8: Cleaning for 3D Applications

The Role of Mass Transfer in Removal of Cross-Linked Sacrificial Layers in 3DI Applications	
M. Sobhian, D.L. Goodman, D. Rabideau and A. Keigler	233
Scaling the 3D Bumps Pitch from 20 to 10 μm, Focusing on the Wet Cu Seed Etch Process Development	
S. Suhard, A. Moussa, J. Slakkeboorn, F. Beirnaert, I. de Preter and F. Holsteys	237
Adhesion Improvement through Plasma Surface Treatments on Palladium Surface	
I. Venegoni, M. Consonni, I. Bianchi, E. Ravizza, S. Grasso, S. Spadoni, M. Pistoni and P. Colpani	241

Chapter 9: Contamination Control and AMC

Control of HF Volatile Contamination in FOUP Environment by Advanced Polymers and Clean Gas Purge	
P. González-Aguirre, H. Fontaine, C. Beitia, J. Ohlsen and J. Lundgren	247
FOUP Material Influence on HF Contamination during Queue-Time	
J. Bounouar, T.Q. Nguyen, O. Le-Barillec, A. Favre, E. Veran, I. Stassen and A. Gettel	251
Effect of FOUP Atmosphere Control on Process Wafer Integrity in Sub20 nm Device Fabrication	
B.H. Kim and J.G. Park	256
Correlation of Cleaning Conditions and Wafer Out-Gassing	
S.H. Han, T.H. Hwang, S.C. Kim, S.H. Park and B.S. Ryu	260
Quantitative Analysis of Transition Metals Penetrating Silicon Substrate through SiN Film by Dopant Ion Implantation and Annealing	
K. Saga, S. Kobayashi and K. Sueoka	265
Collection Efficiency of Noble Metallic Contaminants on Si Wafers with HF-Aqua Regia Mixtures for VPD-DC ICPMS Analysis	
M. Devita, H. Fontaine, N. Drogue, D. Mathiot, V. Enyedi and T. Lardin	268
Backside and Bevel Contamination Removal	
P. Besson, M.C. Roure, R. Kachtouli, M. Jourdan, L. Gabette, A. Royer and V. Loup	272
Focus Spot Reduction by Brush Scrubber Cleaning	
A. Pacco, E. Kesters, I. Simms, K. Nafus, J. Vandereyken and H. Yonekawa	276
Upside-Down Residual Sessile Droplet: Watermarks on Wafers Backside	
N. Belmiloud, E. Schaffert, R. Steininger, K. Okamoto, M. Grothe and G. Koerner	280
Nuclear Magnetic Resonance Spectroscopy of Trace Organic Impurities Extracted from a Corrosion Inhibitor and a Semiaqueous Residue Remover	
G. Westwood	284

Chapter 10: Cleaning and Wet Etching for Semiconductor Photo-Voltaic Cells

Improvement of Silicon Solar Cell Substrates by Wet-Chemical Oxidation Studied by Surface Photovoltage Measurements	
H. Angermann, A. Laades, J. Kegel, C. Klimm and B. Stegemann	291
Simplified Cleaning for a-Si:H Passivation of Wafers Bonded to Glass	
S.N. Granata, T. Bearda, I. Gordon, Y. Abdulraheem, R. Mertens and J. Poortmans	297
Investigation of Silicon Saw Damage Removal and Surface Texturing Using KOH for next Generation Silicon Solar Cells	
M. Haslinger, J. Rip, S. Robert, M. Claes, F. Duerinckx, M. Debucquoy, P.W. Mertens, J. John, D. Pysch, S. Queisser, J. Schweckendiek and A. Hajjiad	300
Impact of Fe and Cu Surface Contamination on High Efficiency Solar Cell Processes	
F. Buchholz and E. Wefringhaus	305
Ozone Base Cleaning: Impact on High Efficiency Interdigitated Back Contact Solar Cells	
B.J. O'Sullivan, M. Haslinger, S. Singh, T. Bearda, M. Debucquoy and J. Szlufcik	312
Rapid Determination of Organic Contaminations on Wafer Surfaces	
S. Meyer, S. Timmel and C. Hagendorf	317
Surface Cleaning and Passivation of Chalcogenide Thin Films Using S(NH₄)₂ Chemical Treatment	
M. Buffiere, A.A. El Mel, N. Lenaers, G. Brammertz, A.E. Zaghi, M. Meuris and J. Poortmans	320